Dielectric properties of hybrid perovskites and drift-diffusion modeling of perovskite cells

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To cite this version:
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ABSTRACT

A method based on DFT is used to obtain dielectric profiles. The high frequency \( \varepsilon(\infty) \) and the static \( \varepsilon(s) \) dielectric profiles are compared for 3D, 2D-3D and 2D Hybrid Organic Perovskites (HOP). A dielectric confinement is observed for the 2D materials between the high dielectric constant of the inorganic part and the low dielectric constant of the organic part. The effect of the ionic contribution on the dielectric constant is also shown. The quantum and dielectric confinements of 3D HOP nanoplatelets are then reported. Finally, a numerical simulation based on the SILVACO code of a HOP based solar cell is proposed for various permittivity of MAPbI\(_3\).

Keywords: Dielectric confinement, Quantum confinement, Nanoplatelets, hybrid Perovskites

1. INTRODUCTION

3D Hybrid Organic Perovskites (HOP) of general formula RMX\(_3\) with R is an organic cation, M is a metal and X a halide have recently attracted a lot of attention in the photovoltaic community due to the fast increase of their efficiency from 3.8 % in 2009\(^1\) to 19.3 % in 2014\(^2\). Actually, the hybrid organic perovskites can be in the 3D or also in the 2D structure. Since the 90s, they are investigated for applications such as Field Effect Transistor (FET)\(^3\) and Light-Emitting Diode (LED)\(^4\). The size of the organic cation R impact directly on the shape of the HOP: for small R (such as CH\(_3\)NH\(_3\)), the 3D structure is preferred whereas for large R (such as C\(_4\)H\(_{12}\)N+) the HOP exhibit a 2D structure with alternating organic and inorganic layers. The structure determines the electronic and optical properties of the HOP such as the excitonic properties. Indeed 2D HOP present an exciton with a large binding energy\(^5\) due to a dielectric confinement\(^6,7\) whereas 3D HOP exhibit an exciton screened by the polar rotation of the organic cations\(^8-10\). We propose here a method to describe dielectric profiles that goes beyond the standard approximation for dielectric constant profiles with abrupt interfaces\(^11,12\). Besides, nanostructures of HOP have been recently reported\(^13-20\). Quantum size effects of nanoplatelets of CH\(_3\)NH\(_3\)PbI\(_3\) are also treated. With the benefit of the all solution process\(^21-23\) of HOP and mature silicon technology\(^24,25\), a cost-effectively and high-efficiency perovskite/Si tandem\(^26-30\) is desirable. The HOP top cell is studied for three different permittivity. The device simulation is based on the SILVACO\(^31\) code dedicated to optoelectronic device design.

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2. INFINITE AND STATIC DIELECTRIC CONSTANT OF 3D AND LAYERED HYBRID PEROVSKITE

The dielectric constant is obtained from the response of the material to an external electric field. Dielectric profiles are computed from an *ab initio* method based on Density Functional Theory (DFT)\textsuperscript{11,32}. An external field is applied to a slab along its stacking axis $z$ inducing a variation of the electron density. The electron density is then averaged in the directions perpendicular to the stacking axis and a nanoscopic average is performed in the direction $z$. The induced polarization $p_{ind}(z)$ is obtained by partial integration of the induced electron density. Finally the dielectric profile is obtained with $ε(z) = \frac{ε_0 E_{ext}}{ε_0 E_{ext} - p_{ind}(z)}$. 

![Figure 1. Figure of the 3D HOP CH$_3$NH$_3$PbI$_3$ (a), the 2D HOP (C$_4$H$_{12}$N)$_2$PbI$_4$ (b) and 2D/3D HOP (C$_{10}$H$_{22}$N)$_2$PbI$_3$ CH$_3$NH$_3$PbI$_4$ (c).](image)

The dielectric constant depends of the frequency of the applied electric field and is described by a tensor for anisotropic system. For optical frequencies, the high frequencies dielectric constant $ε(z)$ is related to the reaction of the electronic density to the electrical field. For lower frequencies, the contribution of the ionic charges are added to the static dielectric constant $ε_s(z)$. Here we propose the dielectric profiles $ε(z)$ and $ε_s(z)$ of HOP with different shape. The systems considered are the 3D HOP CH$_3$NH$_3$PbI$_3$, the 2D HOP (C$_4$H$_{12}$N)$_2$PbI$_4$ and the 2D/3D (C$_{10}$H$_{22}$N)$_2$PbI$_3$CH$_3$NH$_3$PbI$_4$ (Figure 1). The slabs are constructed from the bulk materials: the 3D slab is built from the (010) pnma phase of CH$_3$NH$_3$PbI$_3$ with 6 octahedra PbI$_6$, the 2D/3D slab is composed of 2 two-octahedra inorganic layers sandwiched by aromatic organic cations and the 2D slab is composed of 3 one-octahedron inorganic layers sandwiched by aliphatic organic cations. The profiles $ε(z)$ and $ε_s(z)$ are depicted in the Figure 2. Considering first the high frequency dielectric profile of MAPbI$_3$ (Fig 2.a), the bulk dielectric constant is recovered in the center of the slab with a value about 5.6. It is in good agreement with the measured value of 6.5\textsuperscript{33}. Adding the ionic contribution the dielectric constant obtained is four times higher reaching the value of 22.0 at the center of the slab. This value is closed to the experimental value that oscillates between 23.3 and 37 depending of the sample, the phase and the method\textsuperscript{34-38}. In the case of the 2D HOP, the dielectric constant exhibits a dielectric confinement between the low dielectric constant of the organic part and the high dielectric constant of the inorganic part (Fig 2.c). The 2.1 value obtained for the organic part compares well with experimental values reported around 2-2.3\textsuperscript{37}. The dielectric constant of the inorganic part amounts 4.0 and is as expected lower than the one obtained for the bulk due to dielectric confinement. For lower frequencies, disagreeing to the 3D HOP, the static dielectric constant of the inorganic part is only 2.5 times larger. It can be explained by the anisotropy of the system with an organic layer that softens the ionic displacement response of the inorganic part. Finally the dielectric profiles of the 2D/3D are depicted in fig 2.b. The high frequency dielectric constant reaches 4.8 and stands.
between the 2D and the 3D HOP value. Adding the ionic contribution, the value increases to 15 this is 3 times larger than the infinite one. The enhancement is larger than for the 2D because the system is less anisotropic. We can also note that the ionic contribution is not critical for the organic dielectric constant.

![Graph of dielectric profiles](image)

Figure 2. High frequency dielectric profiles $\varepsilon(z)$ and static dielectric profiles $\varepsilon_s(z)$ for the 3D HOP CH$_3$NH$_3$PbI$_3$ (a), the 2D/3D HOP (C$_x$H$_y$N)$_2$PbI$_4$ (b) and the 2D HOP (C$_z$H$_w$N)$_2$PbI$_4$ (c).

3. DIELECTRIC AND QUANTUM CONFINEMENTS IN NANOPlatelets OF MAPbI$_3$

In this section, we investigate the quantum and dielectric confinement in nanoplatelets of CH$_3$NH$_3$PbI$_3$. Two slabs of 2 and 8 octahedra are constructed from the pnma phase of CH$_3$NH$_3$PbI$_3$. The surface perpendicular to the stacking axis of the slabs corresponds to the (010) direction of the bulk material. The bands structures are shown in the figure 3.a. The two nanoplatelets exhibit a direct band gap at the $\Gamma$ point such as for the bulk material. The energy band gap obtained for 2 octahedra slab is about 2.48 eV and is higher than the thicker one which is amounts 2.07 eV. Figure 3.b. shows the dielectric profiles $\varepsilon(z)$ obtained for the two slabs. The dielectric confinement is due to the reduction of the slab thickness has shown on Fig. 3b from 8 to 2 octahedra. Nanoplatelets of CH$_3$NH$_3$PbI$_3$ were recently reported and an increase of the band gap with decreasing the thickness was observed. However the band gap did not increase as anticipated by various model. It might be explained by an increase of the exciton binding energy which compensates the band gap increase and which is retrieved in our calculations.
Figure 3. Band structures (a) and high frequency dielectric profiles $\varepsilon(z)$ (b) for the slabs of MAPbI$_3$ considered.

4. DIELECTRIC VARIATION ON PEROVSKITE TOP CELL

Silvaco Atlas device simulator is used to numerically solve Poisson’s equation coupled with the continuity equations for both electrons and holes under steady state conditions. Figure 4.a shows the energy band diagrams of MAPbI$_3$ based solar cell under an equilibrium state. The Fermi levels ($E_F$) of each layer are aligned through electron current flowing, while the vacuum levels are shifted according to affinities plus the differences of the conduction bands and $E_F$, or the work-function of electrodes. On the top of FTO cathode (Fig. 4.a), the structure successively consists of 141nm TiO$_2$, 350nm MAPbI$_3$ and 36nm HTM ended with Au anode. The basic parameters of each layer are shown in Table 1, with several permittivity of MAPbI$_3$ according to experimental measurements$^{37,38,39}$ and simulations$^{41}$. The TiO$_2$, MAPbI$_3$ and HTM are assumed to be intrinsic with unintentionally doping level equals to $1e19^{42}$, $1e15^{43,44}$ and $3e18^{45}$. The profile of the refractive image index of MAPbI$_3$ derived from the UV-vis diffuse reflectance spectroscopy$^{46}$.

Table 1: Electronic properties of the multilayers in the MAPbI$_3$ based solar cell cited from literatures. The carrier life time of MAPbI$_3$ are calculated according to the diffusion length and mobility.

<table>
<thead>
<tr>
<th></th>
<th>TiO$_2$</th>
<th>MAPbI$_3$</th>
<th>HTM</th>
</tr>
</thead>
<tbody>
<tr>
<td>Permittivity</td>
<td>85$^{47}$</td>
<td>6.5$^{38,39,47}$</td>
<td>31.9$^{38}$, 70$^{41}$</td>
</tr>
<tr>
<td>Doping level</td>
<td>ND=1e19$^{42}$</td>
<td>NA=1e15$^{48,49}$</td>
<td>NA=3e18$^{55}$</td>
</tr>
<tr>
<td>Affinity eV</td>
<td>4.1$^{49,50}$</td>
<td>3.9</td>
<td>2.05$^{55}$</td>
</tr>
<tr>
<td>Eg, 300K eV</td>
<td>3.5$^{51,52}$</td>
<td>1.48$^{45}$</td>
<td>2.98$^{55}$</td>
</tr>
<tr>
<td>Mobility cm$^2$V$^{-1}$s$^{-1}$</td>
<td>0.2528$^{53}$</td>
<td>6.2$^{54,55}$</td>
<td>0.001$^{47}$</td>
</tr>
<tr>
<td>Carrier life time $\mu$s</td>
<td>0.0006$^{56,57}$</td>
<td>0.1</td>
<td>0.1</td>
</tr>
</tbody>
</table>

Figure 4.b and Table 2 present the photovoltaic results achieved from MAPbI$_3$ based solar cell under 1 sun illumination (AM1.5), with three different permittivity of MAPbI$_3$. By increasing the permittivity of MAPbI$_3$, the $V_{OC}$ is improved more than 6% from 0.981V for the lower permittivity to 1.04 for the higher permittivity. In comparison, the effect on the $J_{sc}$ is almost negligible from 28.81 to 28.95.

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The simplified equivalent circuit model\(^{38}\) for a Photovoltaic Cell reveals that the shunt resistance is not affected too much but the series resistance is decreasing. When the series resistance is decreasing and the shunt resistance is identical, the fill factor is also increasing as one reported on Table 2. As a consequence, the performance of solar cell is improved more than 10%. This value relates well with the experimentally measured efficiency of 17% (CH\(_3\)NH\(_3\)PbI\(_3\))\(^{43}\), well support our simulation for the further investigations of HOP tandem cells.

### Table 2: Photovoltaic results of the MAPbI\(_3\) solar cell studied.

<table>
<thead>
<tr>
<th>Permittivity</th>
<th>J(_{sc}) (mA/cm(^2))</th>
<th>Voc (V)</th>
<th>P(_{max}) (mW)</th>
<th>FF</th>
<th>Eff (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>6.5(^{38,39,47})</td>
<td>28.81</td>
<td>0.981</td>
<td>15.76</td>
<td>0.558</td>
<td>15.88</td>
</tr>
<tr>
<td>31.9(^{38})</td>
<td>28.95</td>
<td>1.023</td>
<td>17.4</td>
<td>0.588</td>
<td>17.52</td>
</tr>
<tr>
<td>70(^{41})</td>
<td>28.95</td>
<td>1.04</td>
<td>17.63</td>
<td>0.586</td>
<td>17.76</td>
</tr>
</tbody>
</table>

## 5. CONCLUSION

In this paper, dielectric profiles of 3D, 2D-3D and 2D Hybrid Organic Perovskites (HOP) are proposed using a method based on DFT calculations. The frequency-dependence of dielectric constant is treated by comparing high frequency \(\varepsilon(z)\) and the static \(\varepsilon_s(z)\) dielectric profiles. A dielectric confinement is found for the layered HOP due to the contrast of the dielectric constant between the organic and the inorganic layers. The quantum and dielectric confinements of 3D HOP nanoplatelets are also investigated. A device simulation of HOP based solar cell is performed. This simulation indicates some key parameters which are important for the optimization of HOP cells performances. An initial optimized HOP based with 17% efficiency is obtained in agreement with experimental measurements.
REFERENCES


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